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/J.R./	Angel M J et al: "Growth of alternating-oriented II-VI Regions of Quasi-Phase-Matched Nonlinear Optical Devices On Gaas Substrates" Applied Physics Letters, American Institute of Physics, NY June 6, 1994.						
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	August 13, 2001						

EXAMINER Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to Applicant.